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(54) **HIGH ELECTRON MOBILITY TRANSISTOR
AND HIGH ELECTRON MOBILITY
TRANSISTOR FORMING METHOD**

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(57)

ABSTRACT

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A high electron mobility transistor (HEMT) and method for forming the same are disclosed. The high electron mobility transistor has a GaN epi-layer, a source ohmic contact, a drain ohmic contact, a gate structure, a first metal electrode contact and a first passivation layer. The source ohmic contact and the drain ohmic contact are disposed on the epi-layer. The gate structure is disposed on the epi-layer and between the source ohmic contact and the drain ohmic contact. The first metal electrode contact is disposed above the gate structure. The first passivation layer is sandwiched between the first metal electrode contact and the gate structure.

